

L Numb r	Hits	S ar h Text	DB	Time stamp
165	2710	substrate same (insulating r di lectri) and (type r onductivity) same (impurity r n ntrati n) sam l ctr de same junction	USPAT; US-PGPUB; EPO; JP ; DERWENT; IBM_TDB	2004/06/10 12:02
166	849	substrate same (insulating or dielectric) and (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:02
167	707	substrate same (insulating or dielectric) and (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:02
168	41	(substrate same (insulating or dielectric) and (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:03
169	35	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:03
170	32	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:04
171	13	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fouth)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:05
172	13	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) sam (third or fourth)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:05

173	9	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:06
174	8	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:06
175	2	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same (control adj electrode) same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:08
176	2	((substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same (control adj electrode) same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm.) and (concentration near2 higher).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:09
177	2	((substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same (control adj electrode) same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm.) and (conductivity).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:09
178	0	(control adj electrode) and (first near conductivity near type) and (second near conductivity near type)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:11
179	0	(control adj electrode) and (first near conductivity near type) and (second near conductivity near type)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:11

180	1333	(control adj el ctrode) and (first near conductivity n ar typ) and (second n ar ondu tivity n ar typ)	USPAT; US-PGPUB; EP ; JPO; DERWENT; IBM_TDB	2004/06/10 12:11
181	137	(c ntrol adj electrode) and (first n ar conductivity near type) and (second near conductivity near type) and ((third or fourth) near2 layer) and ((insulation or insulator or dielectric) near2 (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:12
182	58	(control adj electrode) and (first near conductivity near type) and (second near conductivity near type) and ((third or fourth) near2 layer) and ((insulation or insulator or dielectric) near2 (layer or film)) and ((first or second or third or fourth) near2 concentration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:13
183	27	(control adj electrode).clm. and ((first or scond or third) near conductivity).clm. and ((third or fourth) near2 layer) and ((insulation or insulator or dielectric) near2 (layer or film)) and ((first or second or third or fourth) near2 concentration).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:15
184	96	(control adj electrode).clm. and ((first or scond or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:23
185	53	(control adj electrode).clm. and ((first or scond or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm. and ((third or fourth) near2 layer).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:19
186	26	(control adj electrode).clm. and ((first or scond or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm. and junction.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:34
187	11	(control adj electrode).clm. and ((first or scond or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 c ncentrati n).clm. and (junction same (contr l adj el ctr de)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:35

188	7	(control adj electrode).clm. and ((first or second or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm. and (junction near10 (control adj electrode)).clm.	USPAT; US-PGPUB; EP ; JPO; DERWENT; IBM_TDB	2004/06/10 12:37
189	6	(control adj electrode).clm. and ((first or second or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm. and (junction near10 (control adj electrode)).clm. and (concentration near3 (higher or lower)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:37
190	6	(control adj electrode).clm. and ((first or second or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm. and (junction near10 (control adj electrode)).clm. and (concentration near2 (higher or lower)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:38
191	97	(first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region or layer or portion)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:39
192	63	(first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:41
193	6	(first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and (junction near5 conductivity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:42
194	15	(first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and (junction near10 conductivity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:42
195	0	(first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and (junction near10 conductivity near10 (control adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:43

196	63	(first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and junction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:43
197	29	(first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and junction.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:44
198	5	(first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and (junction same conductivity same (control adj electrode)).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:46
199	3	(first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and (junction same conductivity same (control adj electrode) same ((insulating or insulation or dielectric) near2 (layer or film))).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:47
200	0	(first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and (junction same conductivity same (control adj electrode) same ((insulating or insulation or dielectric) near2 (layer or film))).ti,ab,clm. and capacitance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:47